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December 2014

## **FGL12040WD** 1200 V, 40 A Field Stop Trench IGBT

#### **Features**

- Maximum Junction Temperature: T<sub>J</sub> = 150°C
- · Positive Temperature Co-efficient for Easy Parallel Operating
- Low Saturation Voltage: V<sub>CE(sat)</sub> =2.3 V @ I<sub>C</sub> = 40 A
- 100% of The Parts Tested for  $I_{LM}^{\phantom{LM}(1)}$
- Short Circuit Ruggedness > 5 us @ 150°C
- · High Input Impedance
- · RoHS Compliant

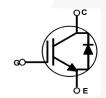
### **General Description**

Using novel field stop IGBT technology, Fairchild's new series of field stop 2<sup>nd</sup> generation IGBTs offer the optimum performance for welder applications where low conduction and switching losses are essential.

### **Applications**

· Only for Welder





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Description		FGL12040WD	Unit
V <sub>CES</sub>	Collector to Emitter Voltage		1200	V
$V_{GES}$	Gate to Emitter Voltage		±25	V
*GES	Transient Gate to Emitter Voltage		±30	V
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25°C	80	А
·C	Collector Current	$@ T_C = 100^{\circ}C$	40	А
I <sub>LM</sub> (1)	Clamped Inductive Load Current	@ T <sub>C</sub> = 25°C	100	Α
I <sub>CM</sub> (2)	Pulsed Collector Current		100	Α
l <sub>F</sub>	Diode Continuous Forward Current	@ T <sub>C</sub> = 25°C	80	А
ı.	Diode Continuous Forward Current	@ T <sub>C</sub> = 100°C	40	А
I <sub>FM</sub> (2)	Diode Maximum Forward Current		100	А
SCWT (3)	Short Circuit Withstand Time @ T <sub>C</sub> = 150°C		5	us
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	391	W
. р	Maximum Power Dissipation $\bigcirc$ T <sub>C</sub> = 100°C		156	W
T <sub>J</sub>	Operating Junction Temperature		-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

- 1. Vcc = 600 V, V<sub>GE</sub> = 15 V, I<sub>C</sub> = 100 A, R<sub>G</sub> = 23  $\Omega$ . Inductive Load 2. Repetitive rating : Pulse width limited by max, junction temperature 3. V<sub>CC</sub> = 600 V, V<sub>GE</sub> = 12 V

### **Thermal Characteristics**

Symbol	Parameter	FGL12040WD	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case	0.32	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case	1.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	25	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGL12040WD	FGL12040WD	TO-264	Tube	-	-	25

### Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	eteristics					
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	V <sub>GE</sub> = 0 V, I <sub>C</sub> = 250 uA	1200	-	-	V
ΔBV <sub>CES</sub> / ΔΤ <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 250 \text{ uA}$	-	1.2	-	V/°C
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0 V	-	-	250	uA
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±400	nA
On Charac	teristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	I <sub>C</sub> = 40 mA, V <sub>CE</sub> = V <sub>GE</sub>	4.8	6.4	8.0	V
		I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V T <sub>C</sub> = 25°C	-	2.3	2.9	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V, T <sub>C</sub> = 150°C	-	2.5	-	٧
Dynamic C	Characteristics					
C <sub>ies</sub>	Input Capacitance		_	2800	-	pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1 MHz	-	105	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	11 - 11VITIZ	-	60	-	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time			45	-	ns
t <sub>r</sub>	Rise Time		-	70	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>CC</sub> = 600 V, I <sub>C</sub> = 40 A,	-	560	- 7	ns
t <sub>f</sub>	Fall Time	$R_G = 23 \Omega, V_{GE} = 15 V,$	-	15	-	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 25°C	-	4.1	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		-	1.0	-	mJ
E <sub>ts</sub>	Total Switching Loss		-	5.1	- 1	mJ
t <sub>d(on)</sub>	Turn-On Delay Time		-	40	-	ns
t <sub>r</sub>	Rise Time		-	65	-	ns
$t_{d(off)}$	Turn-Off Delay Time	$V_{CC} = 600 \text{ V}, I_{C} = 40 \text{ A},$	-	472	-	ns
t <sub>f</sub>	Fall Time	$R_G = 23 \Omega, V_{GE} = 15 V,$	-	51	-	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 150°C	-	6.1	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		-	1.7	-	mJ
E <sub>ts</sub>	Total Switching Loss	1	_	7.8	_	mJ

### **Electrical Characteristics of the IGBT** (Continued)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Qg	Total Gate Charge		-	226	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge	$V_{CE}$ = 600 V, $I_{C}$ = 40 A, $V_{GE}$ = 15 V	-	18	-	nC
Q <sub>gc</sub>	Gate to Collector Charge	VGE - 10 V	-	155	-	nC

### Electrical Characteristics of the DIODE T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>FM</sub>	Diode Forward Voltage	I <sub>F</sub> = 40 A, T <sub>C</sub> = 25°C	-	3.6	4.7	V
1 101		I <sub>F</sub> = 40 A, T <sub>C</sub> = 150°C	-	3.0	-	V
t <sub>rr</sub>	Diode Reverse Recovery Time		-	71	-	ns
I <sub>rr</sub>	Diode Peak Reverse Recovery Current	$V_R = 600 \text{ V}, I_F = 40 \text{ A},$ $di_F/dt = 200 \text{ A/us}, T_C = 25^{\circ}\text{C}$	-	6.8	-	Α
Q <sub>rr</sub>	Diode Reverse Recovery Charge	dif/dt	-	242	-	nC
E <sub>rec</sub>	Reverse Recovery Energy		-	440	-	uJ
t <sub>rr</sub>	Diode Reverse Recovery Time	$V_R = 600 \text{ V}, I_F = 40\text{A},$	-	339	-	ns
I <sub>rr</sub>	Diode Peak Reverse Recovery Current	$di_F/dt = 200 \text{ A/us}, T_C = 150^{\circ}\text{C}$	-	14	-	Α
Q <sub>rr</sub>	Diode Reverse Recovery Charge		-	2373	-	nC

Figure 1. Typical Output Characteristics

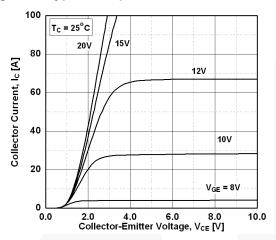


Figure 3. Typical Saturation Voltage Characteristics

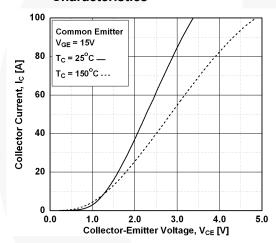
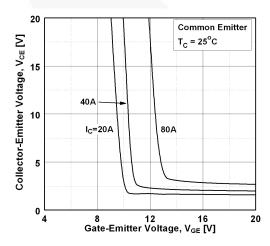


Figure 5. Saturation Voltage vs. V<sub>GE</sub>



**Figure 2. Typical Output Characteristics** 

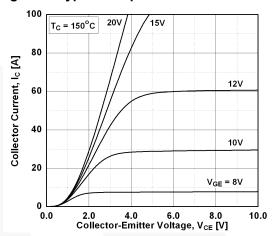


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

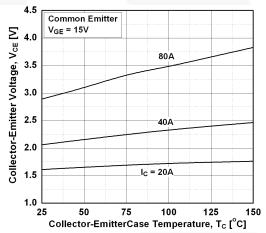


Figure 6. Saturation Voltage vs. V<sub>GE</sub>

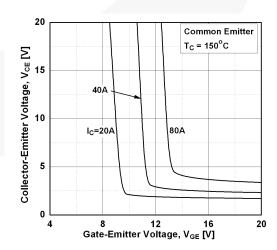
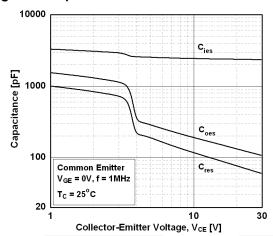


Figure 7. Capacitance Characteristics



**Figure 8. Gate Charge Characteristics** 

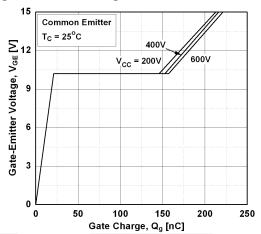


Figure 9. Turn-on Characteristics vs.
Gate Resistance

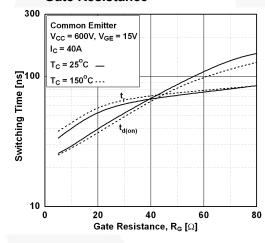


Figure 10. Turn-off Characteristics vs.
Gate Resistance

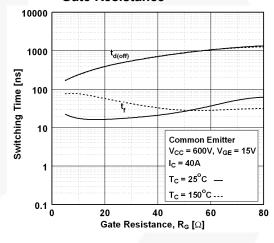


Figure 11. Swithcing Loss vs.

Gate Resistance

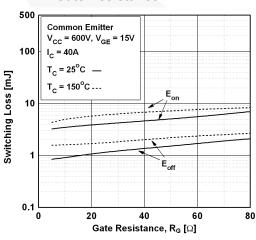


Figure 12. Turn-on Characteristics vs. Collector Current

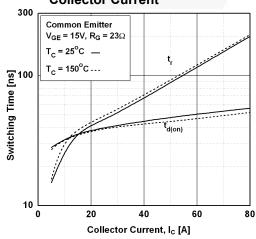


Figure 13. Turn-off Characteristics vs. Collector Current

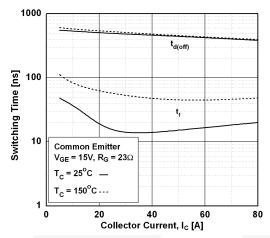


Figure 15. Load Current vs. Frequency

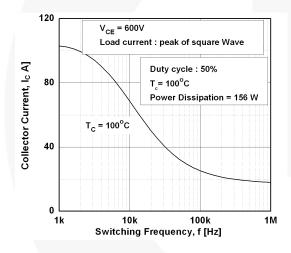


Figure 17. Forward Characteristics

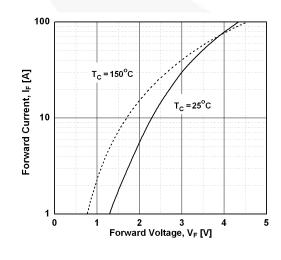


Figure 14. Swithcing Loss vs. Collector Current

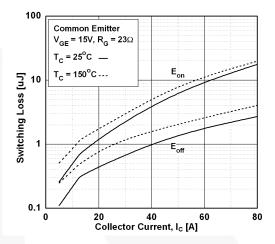


Figure 16. SOA Characteristics

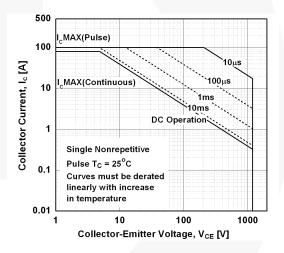


Figure 18. Reverse Recovery Current

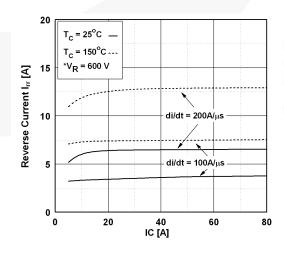


Figure 19. Reverse Recovery Time

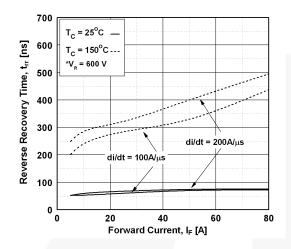


Figure 20. Stored Charge

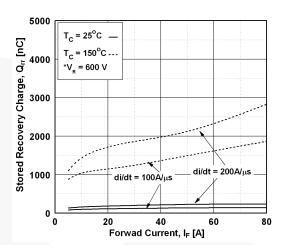


Figure 21. Transient Thermal Impedance of IGBT

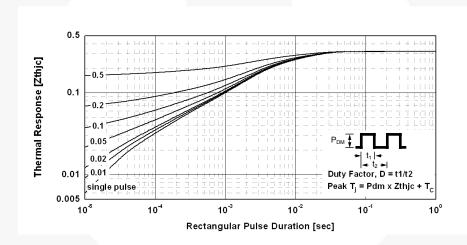
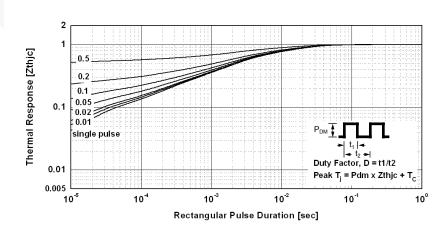


Figure 22. Transient Thermal Impedance of Diode



#### **Mechanical Dimensions** 18.30 5.20 20.20 19.80 17.70 4.80 16.60 Ø<sup>7.40</sup> (1.00) ( 2.00 (12.00 $\phi_{3.10}^{3.50}$ 7.00 <u>C</u> 6.20 5.80 R2.00 C ⊕ 0.254 A B 1.20 0.80 9.10 21.62 (0.50) 8.90 21.02 20.20 19.80 R1.00/C 1.70 1.30 - ( 1.50 ) 2.60 C (4.05) -3.20 2.80 1.50 ) (1.50) 20.50 /c\ 19.50 ⊕ 0.254 M A B 0.85 0.50 5.75 5.75 5.15 5.15 **FRONT VIEW BACK VIEW** SIDE VIEW NOTES: A. PACKAGE REFERENCE: JEDEC TO264 VARIATION AA. B. ALL DIMENSIONS ARE IN MILLIMETERS. 3.70 5.20 (0.15) 3.30 4.80 OUT OF JEDEC STANDARD VALUE. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994. F. THIS PACKAGE IS INTENDED ONLY FOR "FS PKG CODE AR" G. DRAWING FILE NAME: TO264A03REV1 **BOTTOM VIEW**

Figure 23. TO264, Molded, 3-Lead, Jedec Variation AA

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